SILICON PHOTODIODE CHIPS
DEVICE NO. : PD-0090

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-0090

2. Structure :

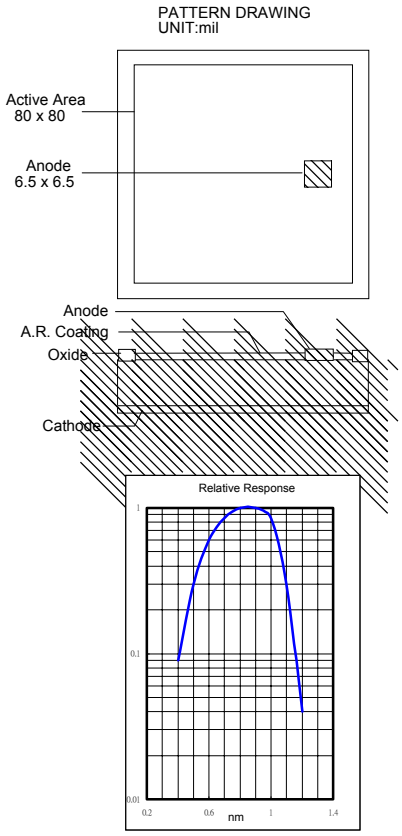
2-1. Planar type : Pin diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy.

3. Size :

3-1. Chip size : 90 mils × 90 mils (2.250 mm × 2.250mm).
3-2. Chip thickness : 12 ± 1.5mils (0.305± 0.038mm).
3-3. Active area : 80mils × 80 mils (2.000 mm × 2.000mm).
3-4. Bonding pad (Anode) : 6.5 mils × 6.5 mils (0.165mm× 0.165 mm)
3-5. Pattern drawing : refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark Current	I_D	V_R=10v H=0mw/ cm^2		5	30	nA
Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA H=0mw/cm^2	33	170		V
Open circuit Voltage	Voc	C_T=2870°k H=5mw/cm^2		390		mV
Short circuit Current	Isc	C_T =2870°k H=5mw/cm^2	30	40		μA
Reverse light Current	I_L	V_R =5V C_T=2870°k H=5mw/cm^2	30	40		μA
Total Capacitance	C_t	V_R =5V H=0mw/cm^2 f=1MHZ		16		pF
Turn-on/ Turn-off Time	t_{on}/t_{off}	V_R=2v R_L=200Ω λ=905nm		250/550		nS



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